

# NCEP02T10D

### **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP02T10D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

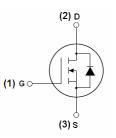
- $V_{DS}$  =200V, $I_{D}$  =100A  $R_{DS(ON)}$  <11mΩ @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-263-2L top view

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02T10D	NCEP02T10D	TO-263-2L	-	-	-

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	200	V
Gate-Source Voltage	V <sub>G</sub> S	±20	V
Drain Current-Continuous	I <sub>D</sub>	100	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	70.7	А
Pulsed Drain Current	I <sub>DM</sub>	400	А
Maximum Power Dissipation	P <sub>D</sub>	300	W
Derating factor		2	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1216	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}\!\mathbb{C}$



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# NCEP02T10D

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	Rejc	0.5	°C/W	Ī
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	200	230	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =200V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =50A	-	10	11	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =50A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -400\/\/ -0\/	-	4200	5500	PF
Output Capacitance	Coss	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V, F=1.0MHz		333.1	450	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			8.8	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	18	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =100 $V$ , $I_{D}$ =50 $A$	-	26	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	41	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	11	-	nS
Total Gate Charge	Qg	\/ -400\/  -504	-	63.2		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =100V,I <sub>D</sub> =50A,	-	24		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V		16.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =100A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	100	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = 50$	-	140		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	_	600		nC

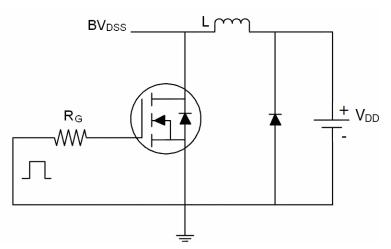
#### Notes:

- ${\it 1. Repetitive Rating: Pulse width limited by maximum junction temperature.}\\$
- 2. Surface Mounted on FR4 Board, t  $\leq$  10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}$ C,V<sub>DD</sub>=50V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

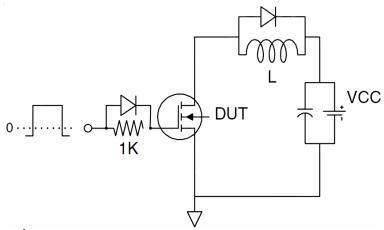


#### **Test Circuit**

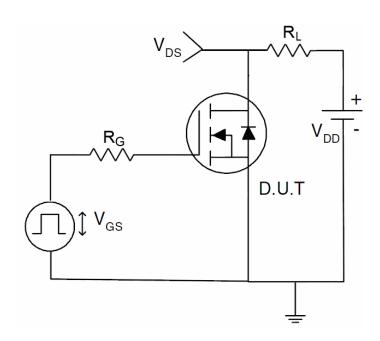
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

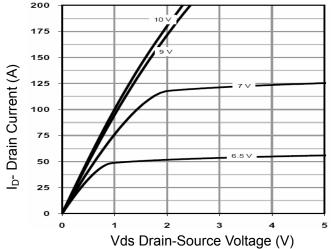


## 3) Switch Time Test Circuit

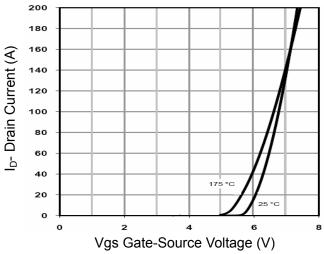








**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

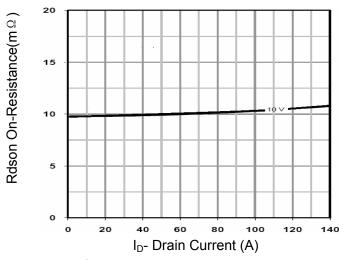


Figure 3 Rdson- Drain Current

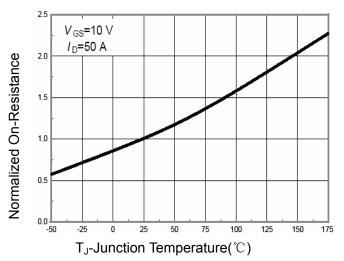


Figure 4 Rdson-JunctionTemperature

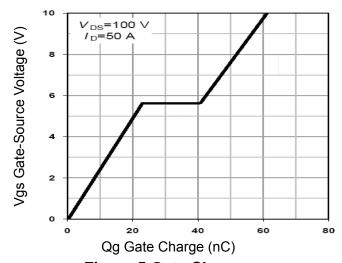


Figure 5 Gate Charge

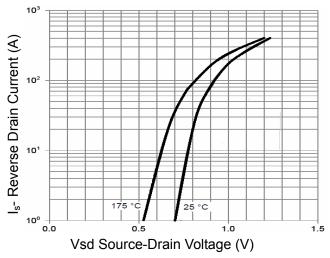
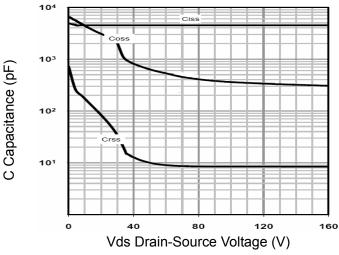


Figure 6 Source- Drain Diode Forward





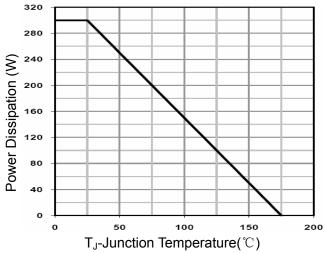
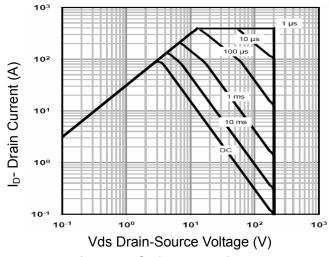


Figure 7 Capacitance vs Vds Figure 9 Power De-rating



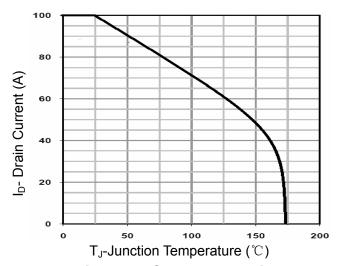


Figure 8 Safe Operation Area

Figure 10 Current De-rating

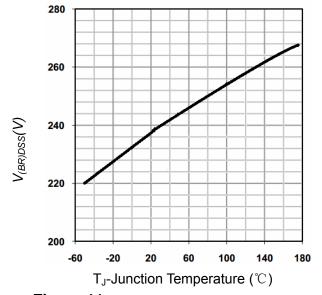
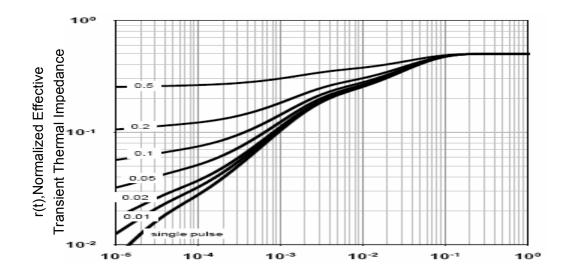


Figure 11 Drain-source breakdown voltage





Square Wave Pluse Duration(sec)

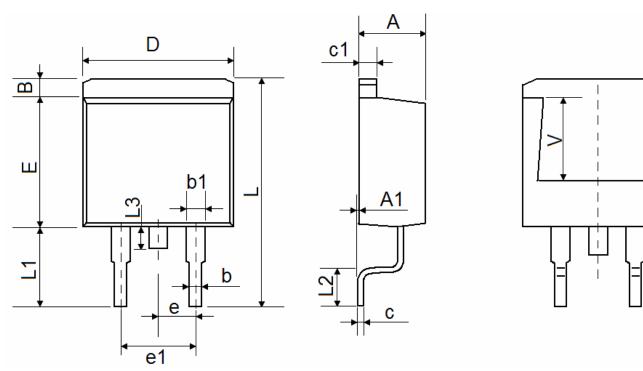
Figure 12 Normalized Maximum Transient Thermal Impedance

**Pb Free Product** 



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**TO-263-2L Package Information** 



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
Α	4.470	4.670	0.176	0.184		
A1	0.000	0.150	0.000	0.006		
В	1.170	1.370	0.046	0.054		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.310	0.530	0.012	0.021		
c1	1.170	1.370	0.046	0.054		
D	10.010	10.310	0.394	0.406		
E	8.500	8.900	0.335	0.350		
е	2.540	TYP.	0.100 T	YP.		
e1	4.980	5.180	0.196	0.204		
L	15.050	15.450	0.593	0.608		
L1	5.080	5.480	0.200	0.216		
L2	2.340	2.740	0.092	0.108		
L3	1.300	1.700	0.051	0.067		
V	5.600	) REF	0.220 F	0.220 REF		



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